Abstracts

1-26 GHz high power p-i-n diode switch

Seung-Won Paek, Hyun-Il Kang, Kye-Ik Jeon, Myung-Deuk Jeong, Dong-Wook Kim, Chae-Rok Lim, Jae-Hak Lee, Won-Sang Lee, Jae-Eung Oh and Ki-Woong Chung. "1-26 GHz high power p-i-n diode switch." 2000 MTT-S International Microwave Symposium Digest 00.1 (2000 Vol. I [MWSYM]): 505-508.

Wideband high power GaAs p-i-n diode SPDT switch is presented. Insertion loss is less than 0.7 dB and isolation is better than -38 dB for 1-26 GHz frequency range. Maximum power handling capability is 35 dBm at 1.8 GHz where the bias voltage is -15 V. Composite buffer layer of superlattice and low temperature grown GaAs prevent the problems of power limitation related to epitaxial buffer layer of p-i-n diode structure.

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